L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT;	2004/04/21 16:25
			US-PGPUB; EPO; JPO; DERWENT	
14	75	(conduct\$6 with (In near5 Ga near5 N))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/04/21 16:25
15	69	(conduct\$6 with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:26
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5 Ga near5 N))	USPAT; EPO; JPO; DERWENT	2004/04/21 16:27
-	131	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/21 16:24
-	20	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/06 11:28
-	28	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	21	((nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6) not ((nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	6	(laser near chip) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:42
_	160	(laser near semiconductor) and (photoelectric or (photo adjelectric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:18
-	14	(laser near semiconductor) and (photoelectric or (photo adjelectric)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:46
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:00
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:03

L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT;	2004/04/21 16:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
14	7 5	(conduct\$6 with (In near5 Ga near5 N))	USPAT;	2004/04/21 16:25
			US-PGPUB;	
			EPO; JPO;	
		(1 .00 .11 /7 5.0 5.3%)	DERWENT	
15	69	(conduct\$6 with (In near5 Ga near5 N))	USPAT;	2004/04/21 16:26
			EPO; JPO;	
16	2	(/1	DERWENT	2004/04/01 16 50
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5	USPAT;	2004/04/21 16:52
		Ga near5 N))	EPO; JPO; DERWENT	
17	3504	(conduct\$7 near1 (layer or region or medium)) and substrate	USPAT:	2004/04/21 16:48
17	3304	and clad\$6	EPO; IPO;	2004/04/21 10:46
		απα ειααφο	DERWENT	
18	42	(conduct\$7 near1 (layer or region or medium)) and substrate	USPAT;	2004/04/21 16:48
		and clad\$6 and (In near5 Ga near5 N)	EPO; IPO;	2001, 01, 21 10:10
		The state and (minority	DERWENT	
19	14	((conduct\$7 near1 (layer or region or medium)) same (In	USPAT;	2004/04/21 16:52
		near5 Ga near5 N))	EPO; JPO;	, , ,
		<i>"</i>	DERWENT	
20	88	In"x"Ga"1-x"N	USPAT;	2004/04/21 16:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
21	3	In"x"Ga"1-x"N and (conduct\$7 near1 (layer or region or	USPAT;	2004/04/21 16:55
		medium)) and substrate and clad\$6	US-PGPUB;	
			EPO; JPO;	
			DERWENT	